



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



FEATURES

- 10 k Ω and 100 k Ω resistance options**
- Resistor tolerance: $\pm 8\%$ maximum**
- Wiper current: ± 6 mA**
- Low temperature coefficient: 35 ppm/ $^{\circ}$ C**
- Wide bandwidth: 3 MHz**
- Fast start-up time <75 μ s**
- Linear gain setting mode**
- Single- and dual-supply operation**
- Independent logic supply: 1.8 V to 5.5 V**
- Wide operating temperature: -40° C to $+125^{\circ}$ C**
- 3 mm \times 3 mm package option**
- Qualified for automotive applications**

APPLICATIONS

- Portable electronics level adjustment**
- LCD panel brightness and contrast controls**
- Programmable filters, delays, and time constants**
- Programmable power supplies**

GENERAL DESCRIPTION

The AD5122/AD5142 potentiometers provide a nonvolatile solution for 128-/256-position adjustment applications, offering guaranteed low resistor tolerance errors of $\pm 8\%$ and up to ± 6 mA current density in the Ax, Bx, and Wx pins.

The low resistor tolerance and low nominal temperature coefficient simplify open-loop applications as well as applications requiring tolerance matching.

The linear gain setting mode allows independent programming of the resistance between the digital potentiometer terminals through the R_{AW} and R_{WB} string resistors, allowing accurate resistor matching.

The high bandwidth and low total harmonic distortion (THD) ensure optimal performance for ac signals, making these devices suitable for filter design.

The low wiper resistance of only 40 Ω at the ends of the resistor array allows pin to pin connection.

The wiper values can be set through an SPI-compatible digital interface that also reads back the wiper register and EEPROM contents.

FUNCTIONAL BLOCK DIAGRAM

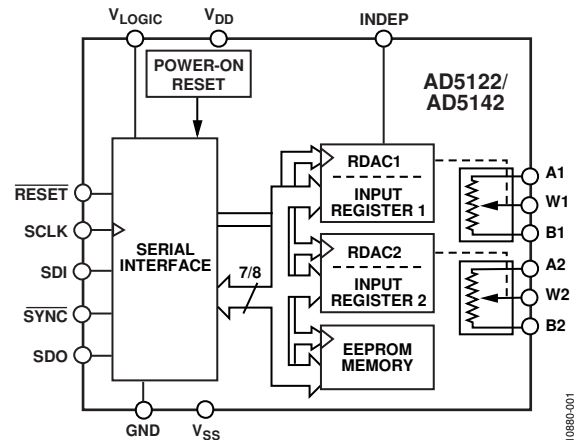


Figure 1.

The AD5122/AD5142 is available in a compact, 16-lead, 3 mm \times 3 mm LFCSP and a 16-lead TSSOP. The devices are guaranteed to operate over the extended industrial temperature range of -40° C to $+125^{\circ}$ C.

Table 1. Family Models

Model	Channel	Position	Interface	Package
AD5123 ¹	Quad	128	I ² C	LFCSP
AD5124	Quad	128	SPI/I ² C	LFCSP
AD5124	Quad	128	SPI	TSSOP
AD5143 ¹	Quad	256	I ² C	LFCSP
AD5144	Quad	256	SPI/I ² C	LFCSP
AD5144	Quad	256	SPI	TSSOP
AD5144A	Quad	256	I ² C	TSSOP
AD5122	Dual	128	SPI	LFCSP/TSSOP
AD5122A	Dual	128	I ² C	LFCSP/TSSOP
AD5142	Dual	256	SPI	LFCSP/TSSOP
AD5142A	Dual	256	I ² C	LFCSP/TSSOP
AD5121	Single	128	SPI/I ² C	LFCSP
AD5141	Single	256	SPI/I ² C	LFCSP

¹ Two potentiometers and two rheostats.

TABLE OF CONTENTS

Features	1	RDAC Register and EEPROM.....	20
Applications.....	1	Input Shift Register	20
Functional Block Diagram	1	SPI Serial Data Interface.....	20
General Description	1	Advanced Control Modes	23
Revision History	2	EEPROM or RDAC Register Protection	24
Specifications.....	3	INDEP Pin.....	24
Electrical Characteristics—AD5122	3	RDAC Architecture.....	27
Electrical Characteristics—AD5142	6	Programming the Variable Resistor.....	27
Interface Timing Specifications	9	Programming the Potentiometer Divider	28
Shift Register and Timing Diagrams	10	Terminal Voltage Operating Range	28
Absolute Maximum Ratings.....	11	Power-Up Sequence	28
Thermal Resistance	11	Layout and Power Supply Biasing	28
ESD Caution.....	11	Outline Dimensions	29
Pin Configurations and Function Descriptions	12	Ordering Guide	30
Typical Performance Characteristics	14	Automotive Products.....	30
Test Circuits.....	19		
Theory of Operation	20		

REVISION HISTORY

6/2016—Rev. A to Rev. B

Changes to Features Section.....	1
Changes to Logic Supply Current Parameter, Table 2	4
Changes to Logic Supply Current Parameter, Table 3	7
Changes to Figure 16.....	15
Added Figure 17; Renumbered Sequentially	15
Changes to Figure 18.....	16
Change to Linear Gain Setting Mode Section	23
Changes to RDAC Architecture Section	27
Changes to Ordering Guide	30
Added Automotive Products Section.....	30

2/2016—Rev. 0 to Rev. A

Changes to Features Section	1
Added Endnote, Table 2	5
Added Endnote, Table 3	8
Added Endnote, Table 4	9
Changes to Figure 3 Caption and Figure 4 Caption	10
Changes to Table 6.....	11
Changes to Figure 6.....	12

10/2012—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—AD5122

$V_{DD} = 2.3 \text{ V to } 5.5 \text{ V}$, $V_{SS} = 0 \text{ V}$; $V_{DD} = 2.25 \text{ V to } 2.75 \text{ V}$, $V_{SS} = -2.25 \text{ V to } -2.75 \text{ V}$; $V_{LOGIC} = 1.8 \text{ V to } 5.5 \text{ V}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Test Conditions/Comments	Min	Typ ¹	Max	Unit
DC CHARACTERISTICS—RHEOSTAT MODE (ALL RDACs)						
Resolution	N		7			Bits
Resistor Integral Nonlinearity ²	R-INL	$R_{AB} = 10 \text{ k}\Omega$				
		$V_{DD} \geq 2.7 \text{ V}$	-1	± 0.1	+1	LSB
		$V_{DD} < 2.7 \text{ V}$	-2.5	± 1	+2.5	LSB
		$R_{AB} = 100 \text{ k}\Omega$				
		$V_{DD} \geq 2.7 \text{ V}$	-0.5	± 0.1	+0.5	LSB
		$V_{DD} < 2.7 \text{ V}$	-1	± 0.25	+1	LSB
Resistor Differential Nonlinearity ²	R-DNL		-0.5	± 0.1	+0.5	LSB
Nominal Resistor Tolerance	$\Delta R_{AB}/R_{AB}$		-8	± 1	+8	%
Resistance Temperature Coefficient ³	$(\Delta R_{AB}/R_{AB})/\Delta T \times 10^6$	Code = full scale		35		ppm/ $^\circ\text{C}$
Wiper Resistance ³	R_W	Code = zero scale				
		$R_{AB} = 10 \text{ k}\Omega$		55	125	Ω
		$R_{AB} = 100 \text{ k}\Omega$		130	400	Ω
Bottom Scale or Top Scale	R_{BS} or R_{TS}	$R_{AB} = 10 \text{ k}\Omega$		40	80	Ω
		$R_{AB} = 100 \text{ k}\Omega$		60	230	Ω
Nominal Resistance Match	R_{AB1}/R_{AB2}	Code = 0xFF	-1	± 0.2	+1	%
DC CHARACTERISTICS—POTENTIOMETER DIVIDER MODE (ALL RDACs)						
Integral Nonlinearity ⁴	INL					
		$R_{AB} = 10 \text{ k}\Omega$	-0.5	± 0.1	+0.5	LSB
		$R_{AB} = 100 \text{ k}\Omega$	-0.25	± 0.1	+0.25	LSB
Differential Nonlinearity ⁴	DNL		-0.25	± 0.1	+0.25	LSB
Full-Scale Error	V_{WFSE}	$R_{AB} = 10 \text{ k}\Omega$	-1.5	-0.1		LSB
		$R_{AB} = 100 \text{ k}\Omega$	-0.5	± 0.1	+0.5	LSB
Zero-Scale Error	V_{WZSE}	$R_{AB} = 10 \text{ k}\Omega$		1	1.5	LSB
		$R_{AB} = 100 \text{ k}\Omega$		0.25	0.5	LSB
Voltage Divider Temperature Coefficient ³	$(\Delta V_W/V_W)/\Delta T \times 10^6$	Code = half scale		± 5		ppm/ $^\circ\text{C}$

Parameter	Symbol	Test Conditions/Comments	Min	Typ ¹	Max	Unit
RESISTOR TERMINALS						
Maximum Continuous Current	I_A , I_B , and I_W	$R_{AB} = 10\text{ k}\Omega$ $R_{AB} = 100\text{ k}\Omega$	-6 -1.5		+6 +1.5	mA mA
Terminal Voltage Range ⁵			V_{SS}		V_{DD}	V
Capacitance A, Capacitance B ³	C_A , C_B	$f = 1\text{ MHz}$, measured to GND, code = half scale $R_{AB} = 10\text{ k}\Omega$ $R_{AB} = 100\text{ k}\Omega$		25 12		pF pF
Capacitance W ³	C_W	$f = 1\text{ MHz}$, measured to GND, code = half scale $R_{AB} = 10\text{ k}\Omega$ $R_{AB} = 100\text{ k}\Omega$		12 5		pF pF
Common-Mode Leakage Current ³		$V_A = V_W = V_B$	-500	± 15	+500	nA
DIGITAL INPUTS						
Input Logic ³						
High	V_{INH}	$V_{LOGIC} = 1.8\text{ V to } 2.3\text{ V}$ $V_{LOGIC} = 2.3\text{ V to } 5.5\text{ V}$	$0.8 \times V_{LOGIC}$ $0.7 \times V_{LOGIC}$			V V
Low	V_{INL}				$0.2 \times V_{LOGIC}$	V
Input Hysteresis ³	V_{HYST}		$0.1 \times V_{LOGIC}$			V
Input Current ³	I_{IN}				± 1	μA
Input Capacitance ³	C_{IN}			5		pF
DIGITAL OUTPUTS						
Output High Voltage ³	V_{OH}	$R_{PULL-UP} = 2.2\text{ k}\Omega$ to V_{LOGIC}		V_{LOGIC}		V
Output Low Voltage ³	V_{OL}	$I_{SINK} = 3\text{ mA}$ $I_{SINK} = 6\text{ mA}$, $V_{LOGIC} > 2.3\text{ V}$			0.4 0.6	V V
Three-State Leakage Current			-1		+1	μA
Three-State Output Capacitance				2		pF
POWER SUPPLIES						
Single-Supply Power Range		$V_{SS} = \text{GND}$	2.3		5.5	V
Dual-Supply Power Range			± 2.25		± 2.75	V
Logic Supply Range		Single supply, $V_{SS} = \text{GND}$ Dual supply, $V_{SS} < \text{GND}$	1.8 2.25		V_{DD} V_{DD}	V V
Positive Supply Current	I_{DD}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$ $V_{DD} = 5.5\text{ V}$ $V_{DD} = 2.3\text{ V}$		0.7 400	5.5	μA nA
Negative Supply Current	I_{SS}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$	-5.5	-0.7		μA
EEPROM Store Current ^{3, 6}	$I_{DD_EEPROM_STORE}$	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		2		mA
EEPROM Read Current ^{3, 7}	$I_{DD_EEPROM_READ}$	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		320		μA
Logic Supply Current	I_{LOGIC}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		0.05	1.4	μA
Power Dissipation ⁸	P_{DISS}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		3.5		μW
Power Supply Rejection Ratio	PSRR	$\Delta V_{DD}/\Delta V_{SS} = V_{DD} \pm 10\%$, code = full scale		-66	-60	dB

Parameter	Symbol	Test Conditions/Comments	Min	Typ ¹	Max	Unit
DYNAMIC CHARACTERISTICS⁹						
Bandwidth	BW	−3 dB R _{AB} = 10 kΩ R _{AB} = 100 kΩ		3 0.43		MHz MHz
Total Harmonic Distortion	THD	V _{DD} /V _{SS} = ±2.5 V, V _A = 1 V rms, V _B = 0 V, f = 1 kHz R _{AB} = 10 kΩ R _{AB} = 100 kΩ		−80 −90		dB dB
Resistor Noise Density	e _{N_WB}	Code = half scale, T _A = 25°C, f = 10 kHz R _{AB} = 10 kΩ R _{AB} = 100 kΩ		7 20		nV/√Hz nV/√Hz
V _W Settling Time	t _S	V _A = 5 V, V _B = 0 V, from zero scale to full scale, ±0.5 LSB error band R _{AB} = 10 kΩ R _{AB} = 100 kΩ		2 12		μs μs
Crosstalk (C _{W1} /C _{W2})	C _T	R _{AB} = 10 kΩ R _{AB} = 100 kΩ		10 25		nV-sec nV-sec
Analog Crosstalk Endurance ¹⁰	C _{TA}	T _A = 25°C		−90 1		dB Mcycles
Data Retention ^{11, 12}			100	50		kcycles Years

¹ Typical values represent average readings at 25°C, V_{DD} = 5 V, V_{SS} = 0 V, and V_{LOGIC} = 5 V.

² Resistor integral nonlinearity (R-INL) error is the deviation from an ideal value measured between the maximum resistance and the minimum resistance wiper positions. R-DNL measures the relative step change from ideal between successive tap positions. The maximum wiper current is limited to (0.7 × V_{DD})/R_{AB}.

³ Guaranteed by design and characterization, not subject to production test.

⁴ INL and DNL are measured at V_{WB} with the RDAC configured as a potentiometer divider similar to a voltage output DAC. V_A = V_{DD} and V_B = 0 V. DNL specification limits of ±1 LSB maximum are guaranteed monotonic operating conditions.

⁵ Resistor Terminal A, Resistor Terminal B, and Resistor Terminal W have no limitations on polarity with respect to each other. Dual-supply operation enables ground referenced bipolar signal adjustment.

⁶ Different from operating current; supply current for EEPROM program lasts approximately 30 ms.

⁷ Different from operating current; supply current for EEPROM read lasts approximately 20 μs.

⁸ P_{DISS} is calculated from (I_{DD} × V_{DD}) + (I_{LOGIC} × V_{LOGIC}).

⁹ All dynamic characteristics use V_{DD}/V_{SS} = ±2.5 V, and V_{LOGIC} = 2.5 V.

¹⁰ Endurance is qualified to 100,000 cycles per JEDEC Standard 22, Method A117 and measured at −40°C to +125°C.

¹¹ Retention lifetime equivalent at junction temperature (T_J) = 125°C per JEDEC Standard 22, Method A117. Retention lifetime, based on an activation energy of 1 eV, derates with junction temperature in the Flash/EE memory.

¹² 50 years applies to an endurance of 1k cycles. An endurance of 100k cycles has an equivalent retention lifetime of 5 years.

ELECTRICAL CHARACTERISTICS—AD5142

$V_{DD} = 2.3 \text{ V to } 5.5 \text{ V}$, $V_{SS} = 0 \text{ V}$; $V_{DD} = 2.25 \text{ V to } 2.75 \text{ V}$, $V_{SS} = -2.25 \text{ V to } -2.75 \text{ V}$; $V_{LOGIC} = 1.8 \text{ V to } 5.5 \text{ V}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$, unless otherwise noted.

Table 3.

Parameter	Symbol	Test Conditions/Comments	Min	Typ ¹	Max	Unit
DC CHARACTERISTICS—RHEOSTAT MODE (ALL RDACS)						
Resolution	N		8			Bits
Resistor Integral Nonlinearity ²	R-INL	$R_{AB} = 10 \text{ k}\Omega$				
		$V_{DD} \geq 2.7 \text{ V}$	-2	± 0.2	+2	LSB
		$V_{DD} < 2.7 \text{ V}$	-5	± 1.5	+5	LSB
Resistor Differential Nonlinearity ²	R-DNL	$R_{AB} = 100 \text{ k}\Omega$				
		$V_{DD} \geq 2.7 \text{ V}$	-1	± 0.1	+1	LSB
		$V_{DD} < 2.7 \text{ V}$	-2	± 0.5	+2	LSB
Nominal Resistor Tolerance	$\Delta R_{AB}/R_{AB}$		-8	± 1	+8	%
Resistance Temperature Coefficient ³	$(\Delta R_{AB}/R_{AB})/\Delta T \times 10^6$	Code = full scale		35		ppm/ $^\circ\text{C}$
Wiper Resistance ³	R_W	Code = zero scale				
		$R_{AB} = 10 \text{ k}\Omega$		55	125	Ω
		$R_{AB} = 100 \text{ k}\Omega$		130	400	Ω
Bottom Scale or Top Scale	R_{BS} or R_{TS}	$R_{AB} = 10 \text{ k}\Omega$		40	80	Ω
		$R_{AB} = 100 \text{ k}\Omega$		60	230	Ω
Nominal Resistance Match	R_{AB1}/R_{AB2}	Code = 0xFF	-1	± 0.2	+1	%
DC CHARACTERISTICS—POTENTIOMETER DIVIDER MODE (ALL RDACS)						
Integral Nonlinearity ⁴	INL	$R_{AB} = 10 \text{ k}\Omega$	-1	± 0.2	+1	LSB
		$R_{AB} = 100 \text{ k}\Omega$	-0.5	± 0.1	+0.5	LSB
Differential Nonlinearity ⁴	DNL		-0.5	± 0.2	+0.5	LSB
Full-Scale Error	V_{WFSE}	$R_{AB} = 10 \text{ k}\Omega$	-2.5	-0.1		LSB
		$R_{AB} = 100 \text{ k}\Omega$	-1	± 0.2	+1	LSB
Zero-Scale Error	V_{WZSE}	$R_{AB} = 10 \text{ k}\Omega$		1.2	3	LSB
		$R_{AB} = 100 \text{ k}\Omega$		0.5	1	LSB
Voltage Divider Temperature Coefficient ³	$(\Delta V_W/V_W)/\Delta T \times 10^6$	Code = half scale		± 5		ppm/ $^\circ\text{C}$

Parameter	Symbol	Test Conditions/Comments	Min	Typ ¹	Max	Unit
RESISTOR TERMINALS						
Maximum Continuous Current	$I_A, I_B, \text{ and } I_W$	$R_{AB} = 10 \text{ k}\Omega$ $R_{AB} = 100 \text{ k}\Omega$	-6 -1.5		+6 +1.5	mA mA
Terminal Voltage Range ⁵			V_{SS}		V_{DD}	V
Capacitance A, Capacitance B ³	C_A, C_B	$f = 1 \text{ MHz}$, measured to GND, code = half scale $R_{AB} = 10 \text{ k}\Omega$ $R_{AB} = 100 \text{ k}\Omega$		25 12		pF pF
Capacitance W ³	C_W	$f = 1 \text{ MHz}$, measured to GND, code = half scale $R_{AB} = 10 \text{ k}\Omega$ $R_{AB} = 100 \text{ k}\Omega$		12 5		pF pF
Common-Mode Leakage Current ³		$V_A = V_W = V_B$	-500	± 15	+500	nA
DIGITAL INPUTS						
Input Logic ³						
High	V_{INH}	$V_{LOGIC} = 1.8 \text{ V to } 2.3 \text{ V}$ $V_{LOGIC} = 2.3 \text{ V to } 5.5 \text{ V}$	$0.8 \times V_{LOGIC}$ $0.7 \times V_{LOGIC}$			V V
Low	V_{INL}				$0.2 \times V_{LOGIC}$	V
Input Hysteresis ³	V_{HYST}		$0.1 \times V_{LOGIC}$			V
Input Current ³	I_{IN}				± 1	μA
Input Capacitance ³	C_{IN}			5		pF
DIGITAL OUTPUTS						
Output High Voltage ³	V_{OH}	$R_{PULL-UP} = 2.2 \text{ k}\Omega \text{ to } V_{LOGIC}$		V_{LOGIC}		V
Output Low Voltage ³	V_{OL}	$I_{SINK} = 3 \text{ mA}$ $I_{SINK} = 6 \text{ mA}, V_{LOGIC} > 2.3 \text{ V}$			0.4 0.6	V V
Three-State Leakage Current			-1		+1	μA
Three-State Output Capacitance				2		pF
POWER SUPPLIES						
Single-Supply Power Range		$V_{SS} = \text{GND}$	2.3		5.5	V
Dual-Supply Power Range			± 2.25		± 2.75	V
Logic Supply Range		Single supply, $V_{SS} = \text{GND}$ Dual supply, $V_{SS} < \text{GND}$	1.8 2.25		V_{DD} V_{DD}	V V
Positive Supply Current	I_{DD}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$ $V_{DD} = 5.5 \text{ V}$ $V_{DD} = 2.3 \text{ V}$		0.7 400	5.5	μA nA
Negative Supply Current	I_{SS}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$	-5.5	-0.7		μA
EEPROM Store Current ^{3, 6}	$I_{DD_EEPROM_STORE}$	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		2		mA
EEPROM Read Current ^{3, 7}	$I_{DD_EEPROM_READ}$	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		320		μA
Logic Supply Current	I_{LOGIC}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		0.05	1.4	μA
Power Dissipation ⁸	P_{DISS}	$V_{IH} = V_{LOGIC}$ or $V_{IL} = \text{GND}$		3.5		μW
Power Supply Rejection Ratio	PSRR	$\Delta V_{DD}/\Delta V_{SS} = V_{DD} \pm 10\%$, code = full scale		-66	-60	dB

Parameter	Symbol	Test Conditions/Comments	Min	Typ ¹	Max	Unit
DYNAMIC CHARACTERISTICS ⁹						
Bandwidth	BW	–3 dB R _{AB} = 10 kΩ R _{AB} = 100 kΩ		3 0.43		MHz MHz
Total Harmonic Distortion	THD	V _{DD} /V _{SS} = ±2.5 V, V _A = 1 V rms, V _B = 0 V, f = 1 kHz R _{AB} = 10 kΩ R _{AB} = 100 kΩ		–80 –90		dB dB
Resistor Noise Density	e _{N_WB}	Code = half scale, T _A = 25°C, f = 10 kHz R _{AB} = 10 kΩ R _{AB} = 100 kΩ		7 20		nV/√Hz nV/√Hz
V _W Settling Time	t _S	V _A = 5 V, V _B = 0 V, from zero scale to full scale, ±0.5 LSB error band R _{AB} = 10 kΩ R _{AB} = 100 kΩ		2 12		μs μs
Crosstalk (C _{W1} /C _{W2})	C _T	R _{AB} = 10 kΩ R _{AB} = 100 kΩ		10 25		nV-sec nV-sec
Analog Crosstalk Endurance ¹⁰	C _{TA}	T _A = 25°C		–90 1		dB Mcycles
Data Retention ^{11, 12}			100	50		kcycles Years

¹ Typical values represent average readings at 25°C, V_{DD} = 5 V, V_{SS} = 0 V, and V_{LOGIC} = 5 V.

² Resistor integral nonlinearity (R-INL) error is the deviation from an ideal value measured between the maximum resistance and the minimum resistance wiper positions. R-DNL measures the relative step change from ideal between successive tap positions. The maximum wiper current is limited to (0.7 × V_{DD})/R_{AB}.

³ Guaranteed by design and characterization, not subject to production test.

⁴ INL and DNL are measured at V_{WB} with the RDAC configured as a potentiometer divider similar to a voltage output DAC. V_A = V_{DD} and V_B = 0 V. DNL specification limits of ±1 LSB maximum are guaranteed monotonic operating conditions.

⁵ Resistor Terminal A, Resistor Terminal B, and Resistor Terminal W have no limitations on polarity with respect to each other. Dual-supply operation enables ground referenced bipolar signal adjustment.

⁶ Different from operating current; supply current for EEPROM program lasts approximately 30 ms.

⁷ Different from operating current; supply current for EEPROM read lasts approximately 20 μs.

⁸ P_{DISS} is calculated from (I_{DD} × V_{DD}) + (I_{LOGIC} × V_{LOGIC}).

⁹ All dynamic characteristics use V_{DD}/V_{SS} = ±2.5 V, and V_{LOGIC} = 2.5 V.

¹⁰ Endurance is qualified to 100,000 cycles per JEDEC Standard 22, Method A117 and measured at –40°C to +125°C.

¹¹ Retention lifetime equivalent at junction temperature (T_J) = 125°C per JEDEC Standard 22, Method A117. Retention lifetime, based on an activation energy of 1 eV, derates with junction temperature in the Flash/EE memory.

¹² 50 years applies to an endurance of 1k cycles. An endurance of 100k cycles has an equivalent retention lifetime of 5 years.

INTERFACE TIMING SPECIFICATIONS

$V_{\text{LOGIC}} = 1.8 \text{ V}$ to 5.5 V ; all specifications T_{MIN} to T_{MAX} , unless otherwise noted.

Table 4. SPI Interface¹

Parameter ²	Test Conditions/Comments	Min	Typ	Max	Unit	Description
t ₁	$V_{\text{LOGIC}} > 1.8 \text{ V}$	20			ns	SCLK cycle time
	$V_{\text{LOGIC}} = 1.8 \text{ V}$	30			ns	
t ₂	$V_{\text{LOGIC}} > 1.8 \text{ V}$	10			ns	SCLK high time
	$V_{\text{LOGIC}} = 1.8 \text{ V}$	15			ns	
t ₃	$V_{\text{LOGIC}} > 1.8 \text{ V}$	10			ns	SCLK low time
	$V_{\text{LOGIC}} = 1.8 \text{ V}$	15			ns	
t ₄		10			ns	$\overline{\text{SYNC}}$ to SCLK falling edge setup time
t ₅		5			ns	Data setup time
t ₆		5			ns	Data hold time
t ₇		10			ns	$\overline{\text{SYNC}}$ rising edge to next SCLK fall ignored
t ₈ ³		20			ns	Minimum $\overline{\text{SYNC}}$ high time
t ₉ ⁴			50		ns	SCLK rising edge to SDO valid
t ₁₀				500	ns	$\overline{\text{SYNC}}$ rising edge to SDO pin disable

¹ Refer to the [AN-1248](#) for additional information about the serial peripheral interface.

² All input signals are specified with $t_r = t_f = 1 \text{ ns/V}$ (10% to 90% of V_{DD}) and timed from a voltage level of $(V_{\text{IL}} + V_{\text{IH}})/2$.

³ Refer to $t_{\text{EEPROM_PROGRAM}}$ and $t_{\text{EEPROM_READBACK}}$ for memory commands operations (see Table 5).

⁴ $R_{\text{PULL_UP}} = 2.2 \text{ k}\Omega$ to V_{DD} with a capacitance load of 168 pF.

Table 5. Control Pins

Parameter	Min	Typ	Max	Unit	Description
t ₁	0.1		10	μs	RESET low time
$t_{\text{EEPROM_PROGRAM}}$ ¹		15	50	ms	Memory program time (not shown in Figure 5)
$t_{\text{EEPROM_READBACK}}$		7	30	μs	Memory readback time (not shown in Figure 5)
$t_{\text{POWER_UP}}$ ²			75	μs	Start-up time (not shown in Figure 5)
t_{RESET}		30		μs	Reset EEPROM restore time (not shown in Figure 5)

¹ EEPROM program time depends on the temperature and EEPROM write cycles. Higher timing is expected at lower temperatures and higher write cycles.

² Maximum time after $V_{\text{DD}} - V_{\text{SS}}$ is equal to 2.3 V.

SHIFT REGISTER AND TIMING DIAGRAMS

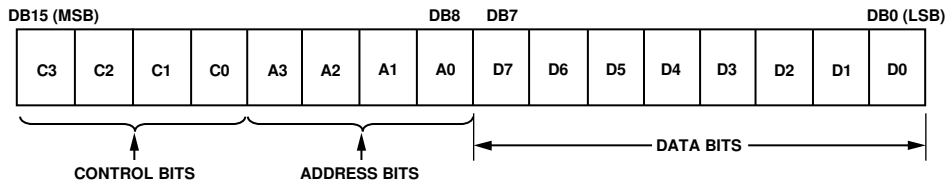


Figure 2. Input Shift Register Contents

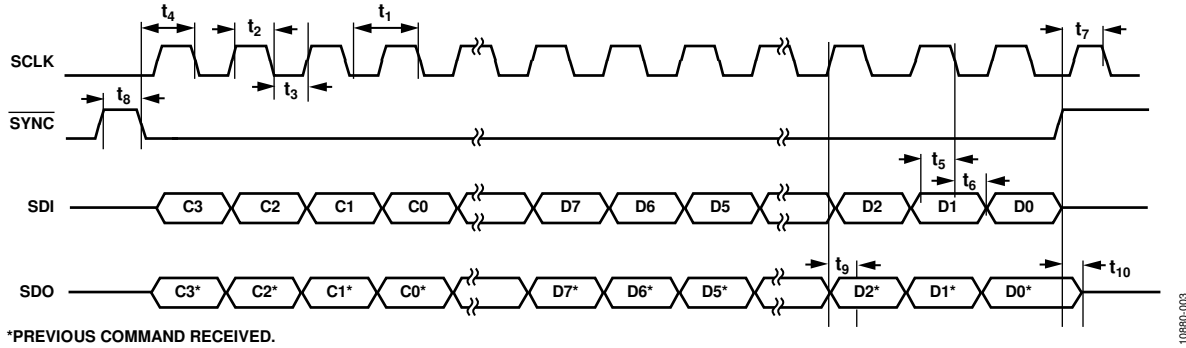


Figure 3. SPI Serial Interface Timing Diagram, Clock Polarity (CPOL) = 0, Clock Phase (CPHA) = 1

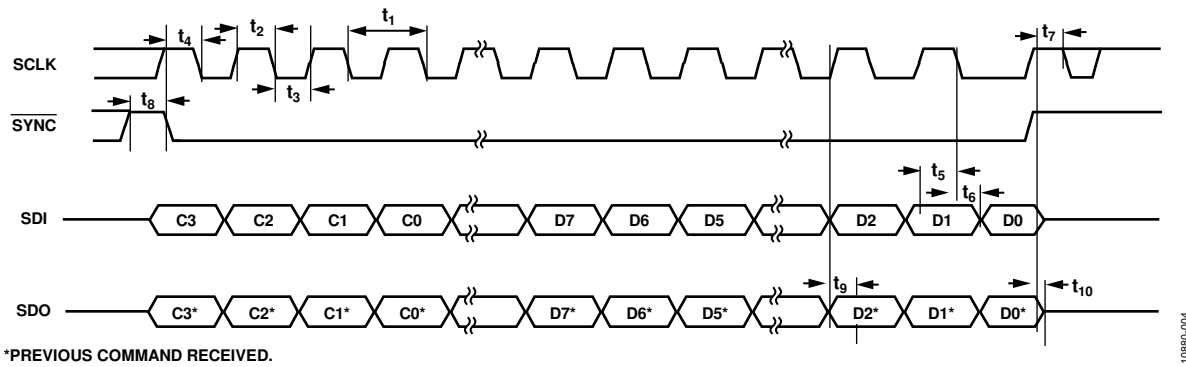


Figure 4. SPI Serial Interface Timing Diagram, Clock Polarity (CPOL) = 1, Clock Phase (CPHA) = 0

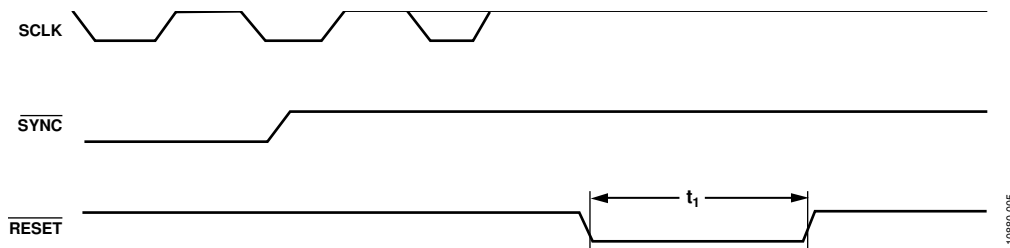


Figure 5. Control Pins Timing Diagram

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 6.

Parameter	Rating
V_{DD} to GND	-0.3 V to +7.0 V
V_{SS} to GND	+0.3 V to -7.0 V
V_{DD} to V_{SS}	7 V
V_{LOGIC} to GND	-0.3 V to $V_{DD} + 0.3$ V or +7.0 V (whichever is less)
V_A, V_W, V_B to GND	$V_{SS} - 0.3$ V, $V_{DD} + 0.3$ V or +7.0 V (whichever is less)
I_A, I_W, I_B	
Pulsed ¹	
Frequency > 10 kHz	
$R_{AW} = 10$ k Ω	± 6 mA/d ²
$R_{AW} = 100$ k Ω	± 1.5 mA/d ²
Frequency ≤ 10 kHz	
$R_{AW} = 10$ k Ω	± 6 mA/ $\sqrt{d^2}$
$R_{AW} = 100$ k Ω	± 1.5 mA/ $\sqrt{d^2}$
Digital Inputs	-0.3 V to $V_{LOGIC} + 0.3$ V or +7 V (whichever is less)
Operating Temperature Range, T_A ³	-40°C to +125°C
Maximum Junction Temperature, T_J Maximum	150°C
Storage Temperature Range	-65°C to +150°C
Reflow Soldering	
Peak Temperature	260°C
Time at Peak Temperature	20 sec to 40 sec
Package Power Dissipation	$(T_J \text{ max} - T_A)/\theta_{JA}$
FICDM	1.5 kV

¹ Maximum terminal current is bounded by the maximum current handling of the switches, maximum power dissipation of the package, and maximum applied voltage across any two of the A, B, and W terminals at a given resistance.

² d = pulse duty factor.

³ Includes programming of EEPROM memory.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

θ_{JA} is defined by the JEDEC JESD51 standard, and the value is dependent on the test board and test environment.

Table 7. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Unit
16-Lead LFCSP	89.5 ¹	3	°C/W
16-Lead TSSOP	150.4 ¹	27.6	°C/W

¹ JEDEC 2S2P test board, still air (0 m/sec airflow).

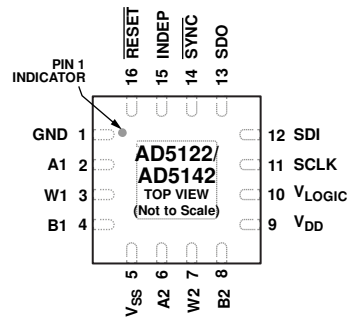
ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS



NOTES
1. INTERNALLY CONNECT THE EXPOSED PAD TO V_{SS} .

10880-006

Figure 6. 16-Lead LFCSP Pin Configuration

Table 8. 16-Lead LFCSP Pin Function Descriptions

Pin No.	Mnemonic	Description
1	GND	Ground Pin, Logic Ground Reference.
2	A1	Terminal A of RDAC1. $V_{SS} \leq V_A \leq V_{DD}$.
3	W1	Wiper Terminal of RDAC1. $V_{SS} \leq V_W \leq V_{DD}$.
4	B1	Terminal B of RDAC1. $V_{SS} \leq V_B \leq V_{DD}$.
5	V_{SS}	Negative Power Supply. Decouple this pin with 0.1 μF ceramic capacitors and 10 μF capacitors.
6	A2	Terminal A of RDAC2. $V_{SS} \leq V_A \leq V_{DD}$.
7	W2	Wiper Terminal of RDAC2. $V_{SS} \leq V_W \leq V_{DD}$.
8	B2	Terminal B of RDAC2. $V_{SS} \leq V_B \leq V_{DD}$.
9	V_{DD}	Positive Power Supply. Decouple this pin with 0.1 μF ceramic capacitors and 10 μF capacitors.
10	V_{LOGIC}	Logic Power Supply; 1.8 V to V_{DD} . Decouple this pin with 0.1 μF ceramic capacitors and 10 μF capacitors.
11	SCLK	Serial Clock Line. Data is clocked in at the logic low transition.
12	SDI	Serial Data Input.
13	$\overline{\text{SDO}}$	Serial Data Output. This is an open-drain output pin, and it needs an external pull-up resistor.
14	$\overline{\text{SYNC}}$	Synchronization Input, Active Low. When $\overline{\text{SYNC}}$ returns high, data is loaded into the input shift register.
15	INDEP	Linear Gain Setting Mode at Power-Up. Each string resistor is loaded independently from the associated memory location. If INDEP is enabled, it cannot be disabled by software.
16	$\overline{\text{RESET}}$	Hardware Reset Pin. Refresh the RDAC registers from EEPROM. $\overline{\text{RESET}}$ is activated at the logic low. If this pin is not used, tie $\overline{\text{RESET}}$ to V_{LOGIC} .
	EPAD	Internally Connect the Exposed Pad to V_{SS} .

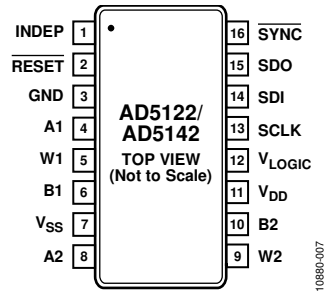


Figure 7. 16-Lead TSSOP, SPI Interface Pin Configuration

Table 9. 16-Lead TSSOP, SPI Interface Pin Function Descriptions

Pin No.	Mnemonic	Description
1	INDEP	Linear Gain Setting Mode at Power-Up. Each string resistor is loaded independently from the associated memory location. If INDEP is enabled, it cannot be disabled by software.
2	$\overline{\text{RESET}}$	Hardware Reset Pin. Refresh the RDAC registers from EEPROM. $\overline{\text{RESET}}$ is activated at the logic low. If this pin is not used, tie $\overline{\text{RESET}}$ to V_{LOGIC} .
3	GND	Ground Pin, Logic Ground Reference.
4	A1	Terminal A of RDAC1. $V_{\text{SS}} \leq V_A \leq V_{\text{DD}}$.
5	W1	Wiper Terminal of RDAC1. $V_{\text{SS}} \leq V_W \leq V_{\text{DD}}$.
6	B1	Terminal B of RDAC1. $V_{\text{SS}} \leq V_B \leq V_{\text{DD}}$.
7	V_{SS}	Negative Power Supply. Decouple this pin with 0.1 μF ceramic capacitors and 10 μF capacitors.
8	A2	Terminal A of RDAC2. $V_{\text{SS}} \leq V_A \leq V_{\text{DD}}$.
9	W2	Wiper Terminal of RDAC2. $V_{\text{SS}} \leq V_W \leq V_{\text{DD}}$.
10	B2	Terminal B of RDAC2. $V_{\text{SS}} \leq V_B \leq V_{\text{DD}}$.
11	V_{DD}	Positive Power Supply. Decouple this pin with 0.1 μF ceramic capacitors and 10 μF capacitors.
12	V_{LOGIC}	Logic Power Supply; 1.8 V to V_{DD} . Decouple this pin with 0.1 μF ceramic capacitors and 10 μF capacitors.
13	SCLK	Serial Clock Line. Data is clocked in at the logic low transition.
14	SDI	Serial Data Input.
15	$\overline{\text{SDO}}$	Serial Data Output. This is an open-drain output pin, and it needs an external pull-up resistor.
16	$\overline{\text{SYNC}}$	Synchronization Input, Active Low. When $\overline{\text{SYNC}}$ returns high, data is loaded into the input shift register.

TYPICAL PERFORMANCE CHARACTERISTICS

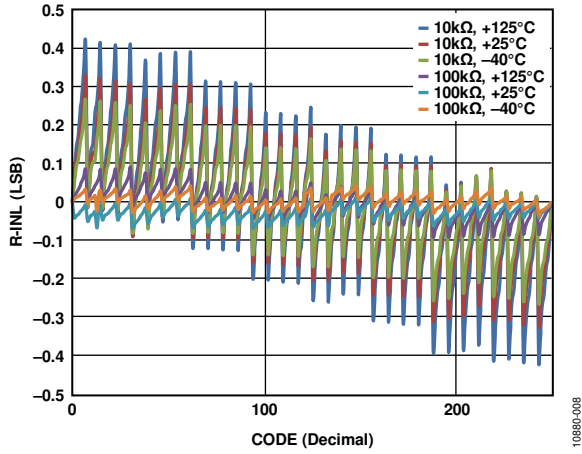


Figure 8. R-INL vs. Code (AD5142)

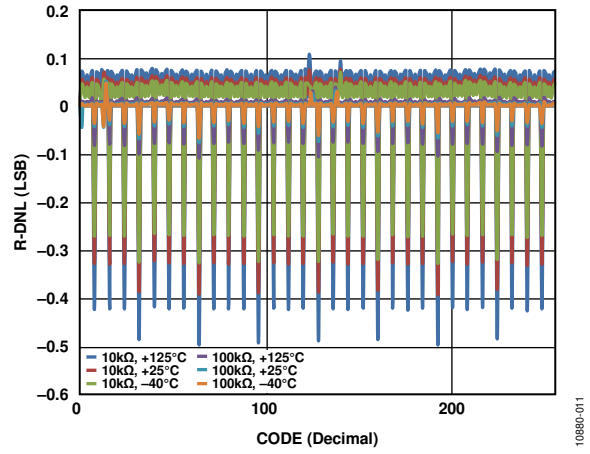


Figure 11. R-DNL vs. Code (AD5142)

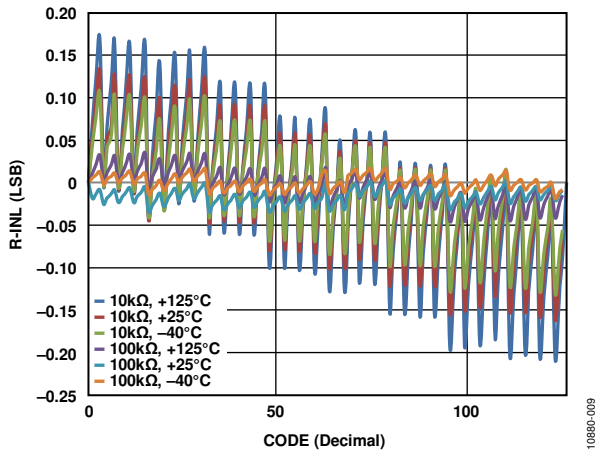


Figure 9. R-INL vs. Code (AD5122)

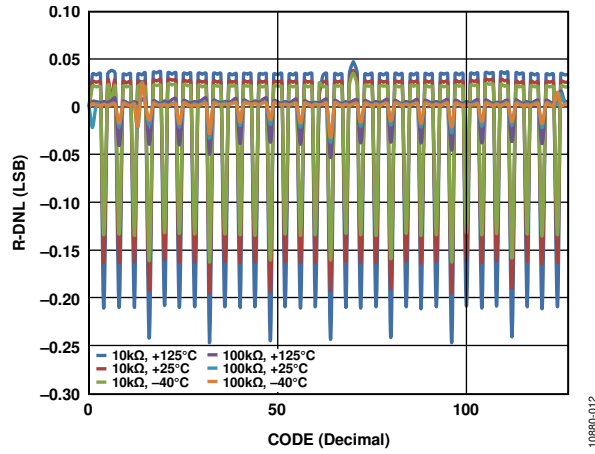


Figure 12. R-DNL vs. Code (AD5122)

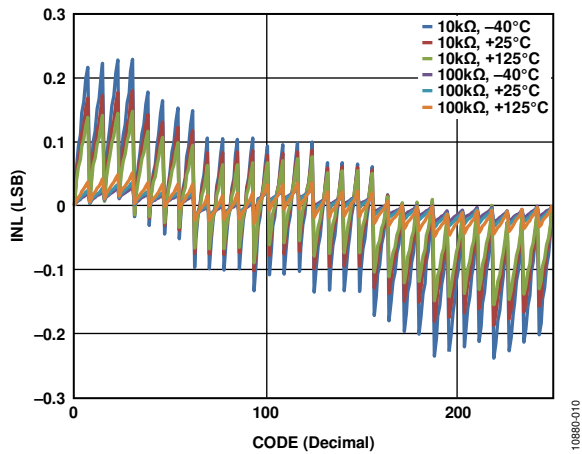


Figure 10. INL vs. Code (AD5142)

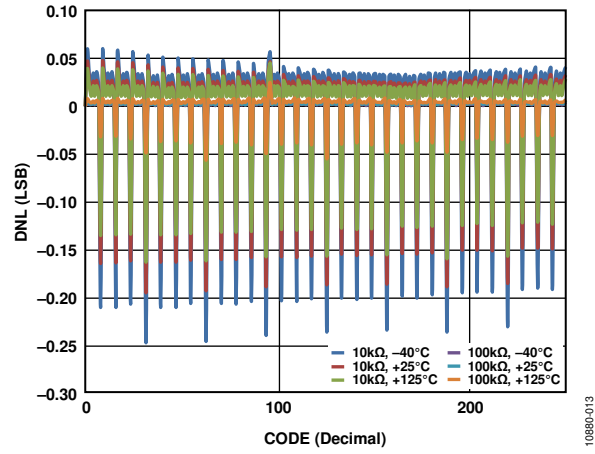


Figure 13. DNL vs. Code (AD5142)

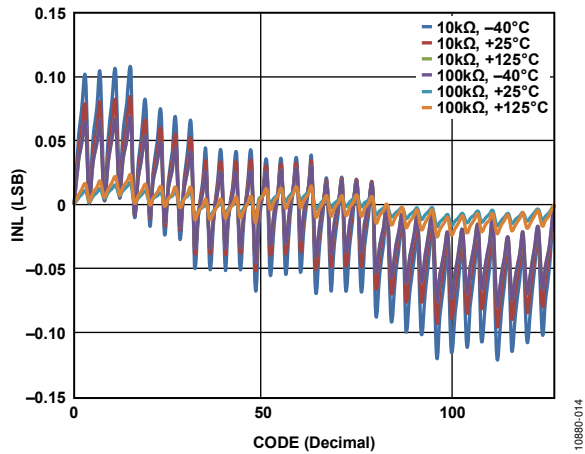


Figure 14. INL vs. Code (AD5122)

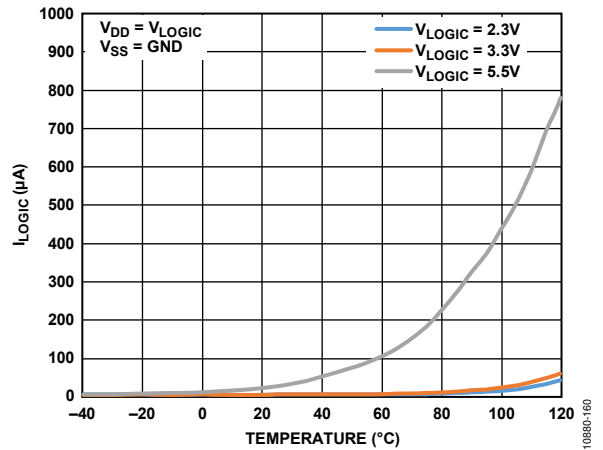


Figure 17. I_{LOGIC} Current vs. Temperature

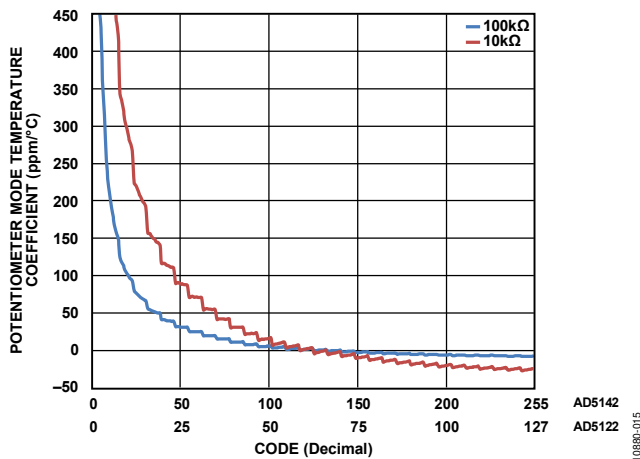


Figure 15. Potentiometer Mode Temperature Coefficient $((\Delta V_W/V_W)/\Delta T \times 10^6)$ vs. Code

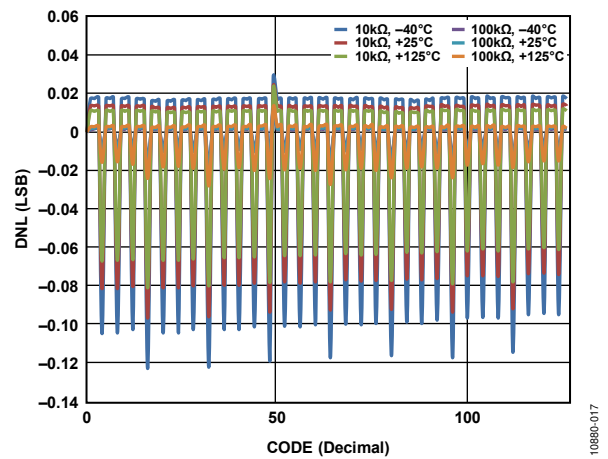


Figure 18. DNL vs. Code (AD5122)

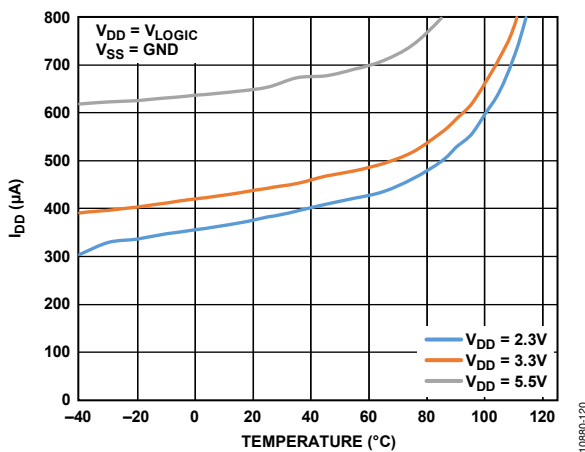


Figure 16. Supply Current vs. Temperature

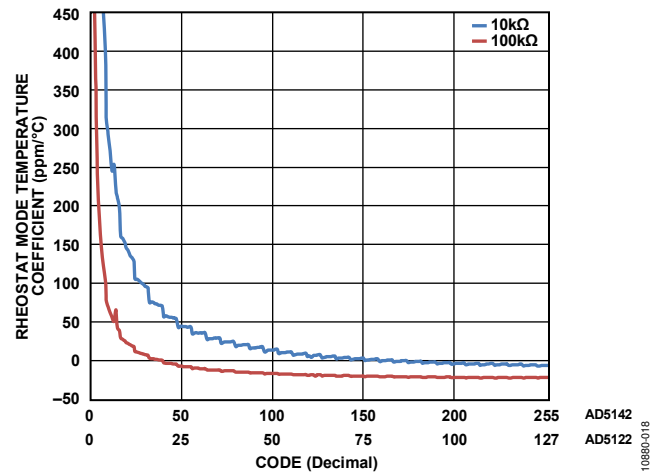


Figure 19. Rheostat Mode Temperature Coefficient $((\Delta R_{WB}/R_{WB})/\Delta T \times 10^6)$ vs. Code

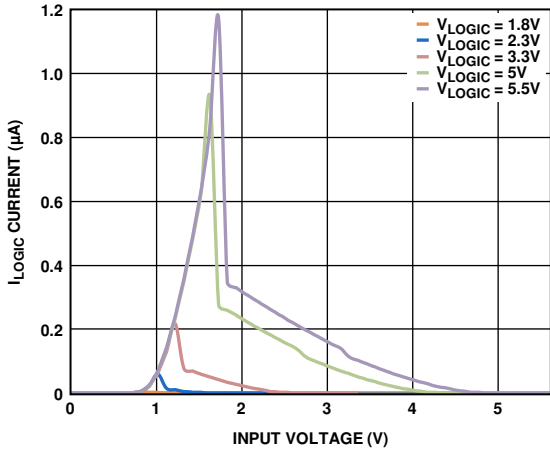


Figure 20. I_{LOGIC} Current vs. Digital Input Voltage

1088B-019

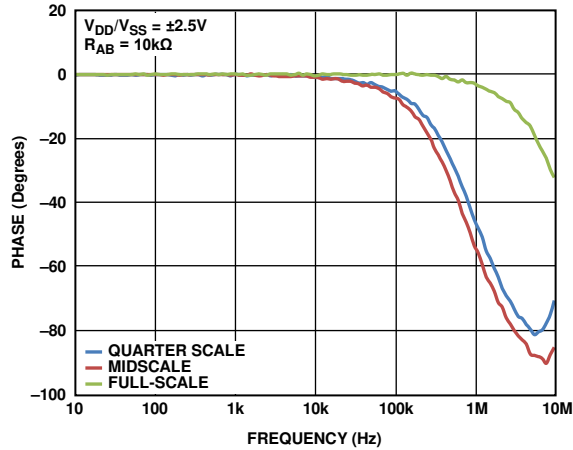


Figure 23. Normalized Phase Flatness vs. Frequency, $R_{AB} = 10\text{ k}\Omega$

1088B-022

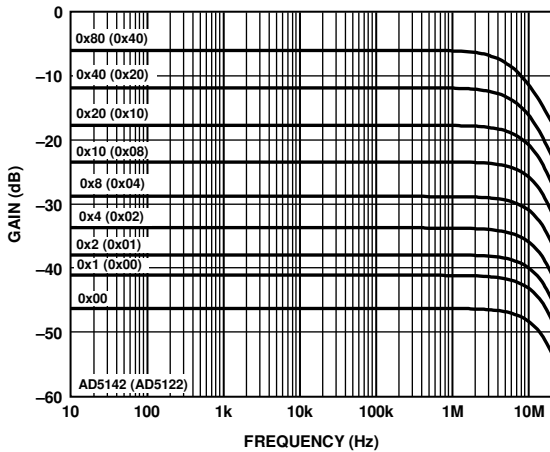


Figure 21. $10\text{ k}\Omega$ Gain vs. Frequency vs. Code

1088B-020

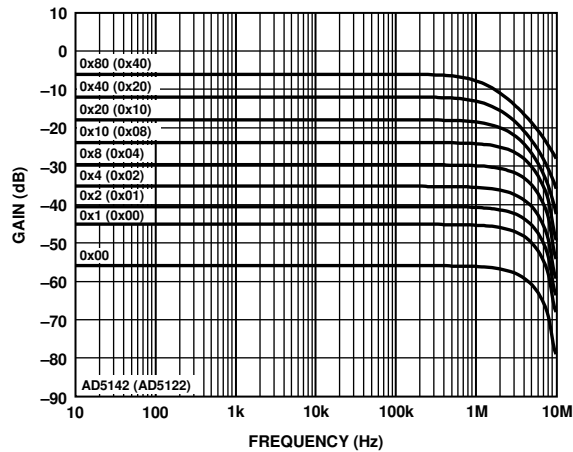


Figure 24. $100\text{ k}\Omega$ Gain vs. Frequency vs. Code

1088B-023

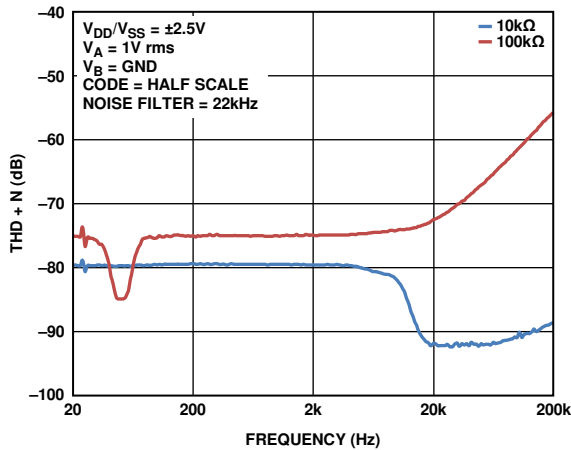


Figure 22. Total Harmonic Distortion Plus Noise (THD + N) vs. Frequency

1088B-021

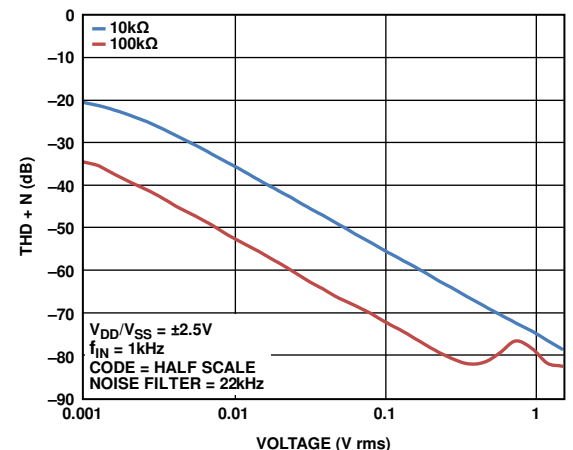


Figure 25. Total Harmonic Distortion Plus Noise (THD + N) vs. Amplitude

1088B-024

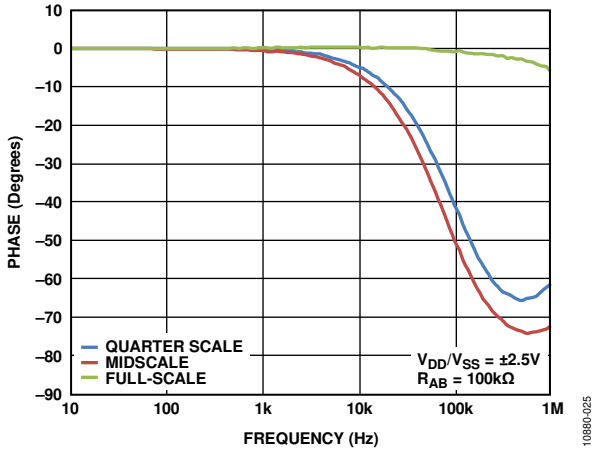


Figure 26. Normalized Phase Flatness vs. Frequency, $R_{AB} = 100\text{ k}\Omega$

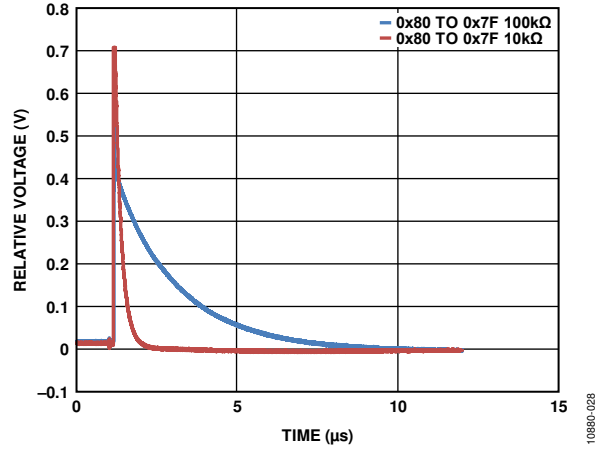


Figure 29. Maximum Transition Glitch

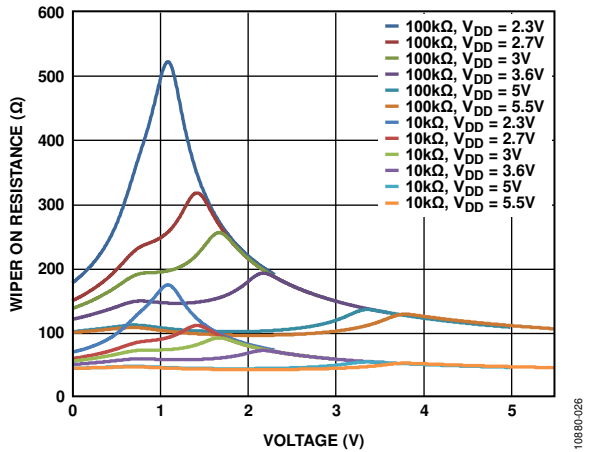


Figure 27. Incremental Wiper On Resistance vs. Positive Power Supply (V_{DD})

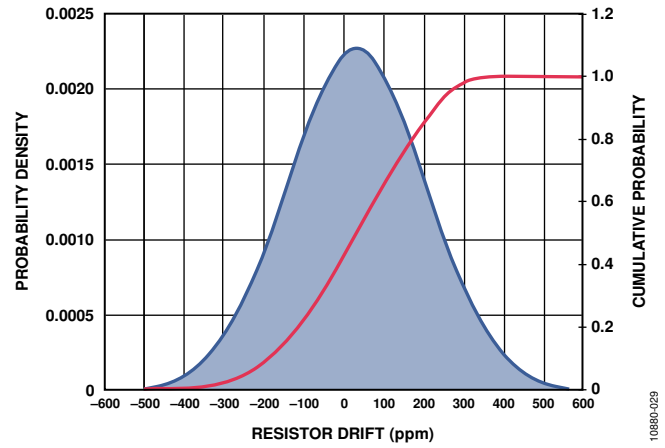


Figure 30. Resistor Lifetime Drift

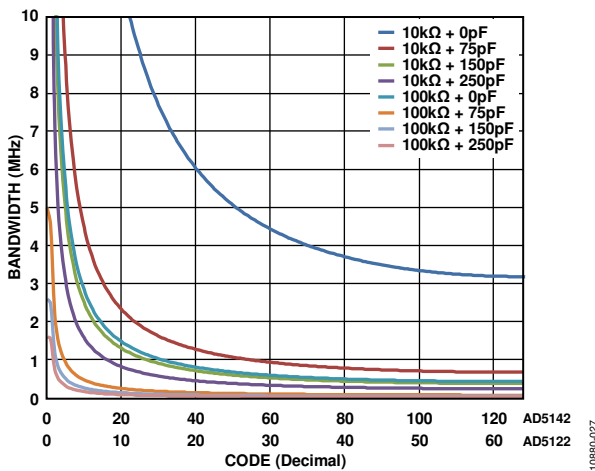


Figure 28. Maximum Bandwidth vs. Code vs. Net Capacitance

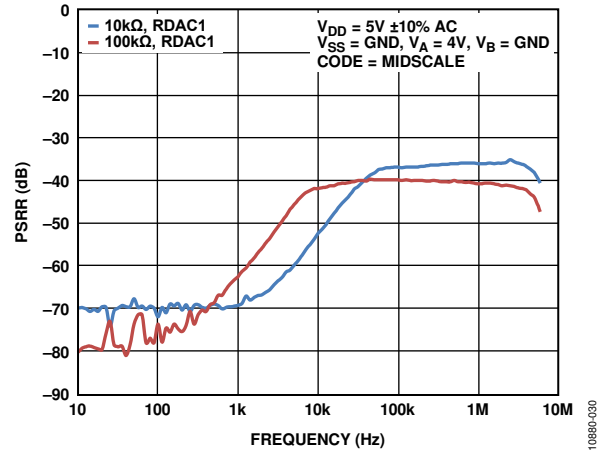


Figure 31. Power Supply Rejection Ratio (PSRR) vs. Frequency

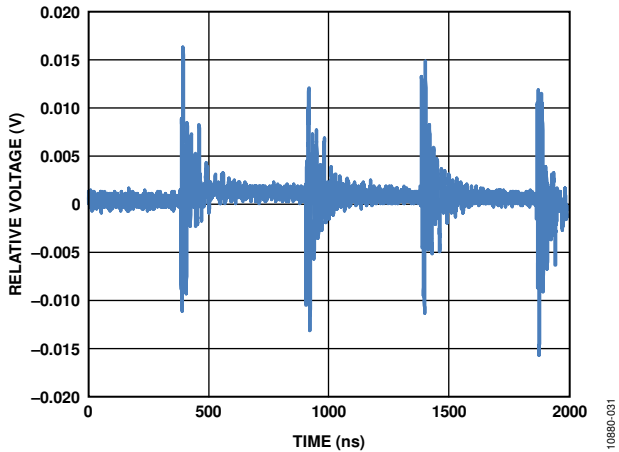


Figure 32. Digital Feedthrough

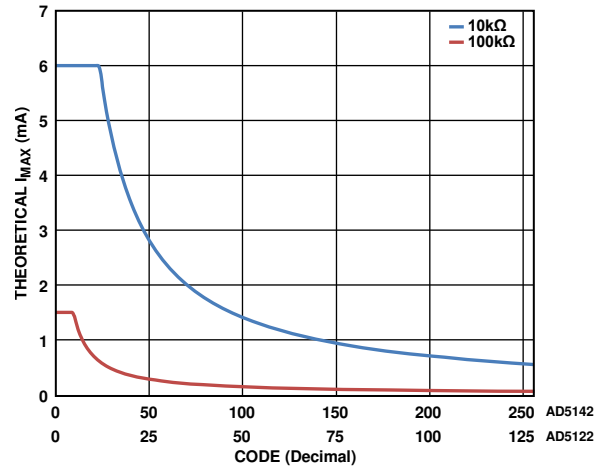


Figure 34. Theoretical Maximum Current vs. Code

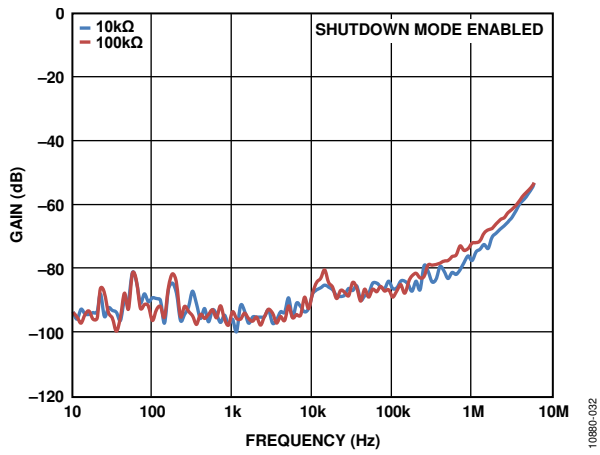


Figure 33. Shutdown Isolation vs. Frequency

TEST CIRCUITS

Figure 35 to Figure 39 define the test conditions used in the Specifications section.

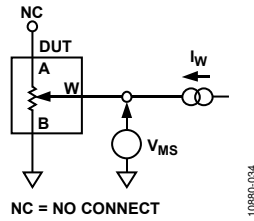


Figure 35. Resistor Integral Nonlinearity Error (Rheostat Operation; R-INL, R-DNL)

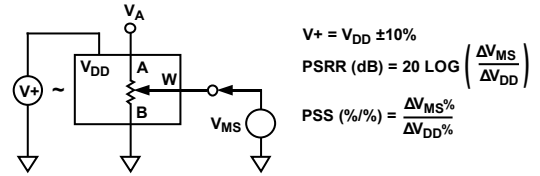


Figure 38. Power Supply Sensitivity and Power Supply Rejection Ratio (PSS, PSRR)

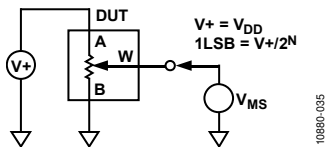


Figure 36. Potentiometer Divider Nonlinearity Error (INL, DNL)

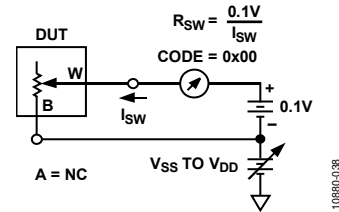


Figure 39. Incremental On Resistance

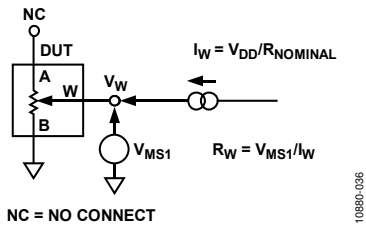


Figure 37. Wiper Resistance

THEORY OF OPERATION

The [AD5122/AD5142](#) digital programmable potentiometers are designed to operate as true variable resistors for analog signals within the terminal voltage range of $V_{SS} < V_{TERM} < V_{DD}$. The resistor wiper position is determined by the RDAC register contents. The RDAC register acts as a scratchpad register that allows unlimited changes of resistance settings. A secondary register (the input register) can preload the RDAC register data.

The RDAC register can be programmed with any position setting using the SPI interface (depending on the model). When a desirable wiper position is found, this value can be stored in the EEPROM memory. Thereafter, the wiper position is always restored to that position for subsequent power-ups. The storing of EEPROM data takes approximately 15 ms; during this time, the device is locked and does not acknowledge any new command, preventing any changes from taking place.

RDAC REGISTER AND EEPROM

The RDAC register directly controls the position of the digital potentiometer wiper. For example, when the RDAC register is loaded with 0x80 ([AD5142](#), 256 taps), the wiper is connected to half scale of the variable resistor. The RDAC register is a standard logic register; there is no restriction on the number of changes allowed.

It is possible to both write to and read from the RDAC register using the digital interface (see Table 10).

The contents of the RDAC register can be stored to the EEPROM using Command 9 (see Table 16). Thereafter, the RDAC register always sets at that position for any future on-off-on power supply sequence. It is possible to read back data saved into the EEPROM with Command 3 (see Table 10).

Alternatively, the EEPROM can be written to independently using Command 11 (see Table 16).

INPUT SHIFT REGISTER

For the [AD5122/AD5142](#), the input shift register is 16 bits wide, as shown in Figure 2. The 16-bit word consists of four control bits, followed by four address bits and by eight data bits.

If the [AD5122](#) RDAC or EEPROM registers are read from or written to, the lowest data bit (Bit 0) is ignored.

Data is loaded MSB first (Bit 15). The four control bits determine the function of the software command as listed in Table 10 and Table 16.

SPI SERIAL DATA INTERFACE

The [AD5122/AD5142](#) contain a 4-wire, SPI-compatible digital interface (SDI, $\overline{\text{SYNC}}$, SDO, and SCLK). The write sequence begins by bringing the $\overline{\text{SYNC}}$ line low. The $\overline{\text{SYNC}}$ pin must be held low until the complete data-word is loaded from the SDI pin. Data is loaded in at the SCLK falling edge transition, as shown in Figure 3 and Figure 4. When $\overline{\text{SYNC}}$ returns high, the serial data-word is decoded according to the instructions in Table 16.

To minimize power consumption in the digital input buffers when the device is enabled, operate all serial interface pins close to the V_{LOGIC} supply rails.

$\overline{\text{SYNC}}$ Interruption

In a standalone write sequence for the [AD5122/AD5142](#), the $\overline{\text{SYNC}}$ line is kept low for 16 falling edges of SCLK, and the instruction is decoded when $\overline{\text{SYNC}}$ is pulled high. However, if the $\overline{\text{SYNC}}$ line is kept low for less than 16 falling edges of SCLK, the input shift register content is ignored, and the write sequence is considered invalid.

SDO Pin

The serial data output pin (SDO) serves two purposes: to read back the contents of the control, EEPROM, RDAC, and input registers using Command 3 (see Table 10 and Table 16), and to connect the [AD5122/AD5142](#) to daisy-chain mode.

The SDO pin contains an internal open-drain output that needs an external pull-up resistor. The SDO pin is enabled when $\overline{\text{SYNC}}$ is pulled low, and the data is clocked out of SDO on the rising edge of SCLK, as shown in Figure 3 and Figure 4.

Daisy-Chain Connection

Daisy chaining minimizes the number of port pins required from the controlling IC. As shown in Figure 40, the SDO pin of one package must be tied to the SDI pin of the next package. The clock period can be increased because of the propagation delay of the line between subsequent devices. When two AD5122/AD5142 devices are daisy chained, 32 bits of data are required. The first 16 bits assigned to U2, and the second 16 bits assigned to U1, as shown in Figure 41. Keep the SYNC pin low until all 32 bits are clocked into their respective serial registers. The SYNC pin is then pulled high to complete the operation. A typical connection is shown in Figure 40.

To prevent data from mislocking (for example, due to noise) the device includes an internal counter, if the clock falling edges count is not a multiple of 8, the device ignores the command. A valid clock count is 16, 24, or 32. The counter resets when SYNC returns high.

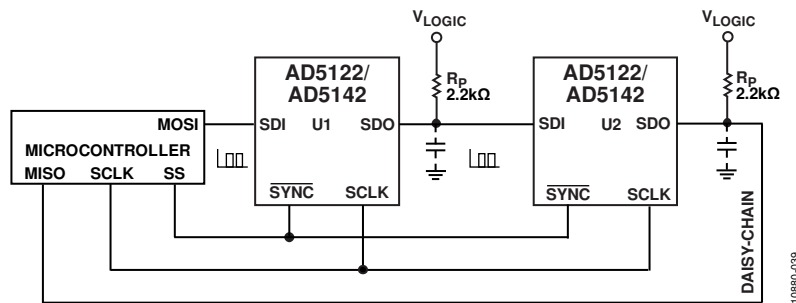


Figure 40. Daisy-Chain Configuration

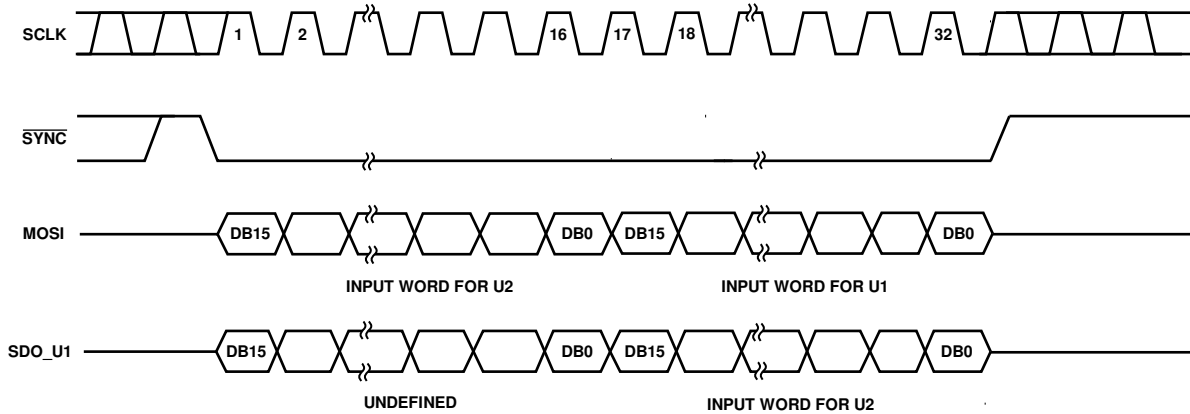


Figure 41. Daisy-Chain Diagram

Table 10. Reduced Commands Operation Truth Table

Command Number	Control Bits[DB15:DB12]				Address Bits[DB11:DB8] ¹				Data Bits[DB7:DB0] ¹								Operation		
	C3	C2	C1	C0	A3	A2	A1	A0	D7	D6	D5	D4	D3	D2	D1	D0			
0	0	0	0	0	X	X	X	X	X	X	X	X	X	X	X	X	NOP: do nothing.		
1	0	0	0	1	0	0	0	A0	D7	D6	D5	D4	D3	D2	D1	D0	Write contents of serial register data to RDAC		
2	0	0	1	0	0	0	0	A0	D7	D6	D5	D4	D3	D2	D1	D0	Write contents of serial register data to input register		
3	0	0	1	1	X	0	A1	A0	X	X	X	X	X	X	D1	D0	Read back contents		
																	D1	D0	Data
																	0	1	EEPROM
																	1	1	RDAC
9	0	1	1	1	0	0	0	A0	X	X	X	X	X	X	X	X	1	Copy RDAC register to EEPROM	
10	0	1	1	1	0	0	0	A0	X	X	X	X	X	X	X	X	0	Copy EEPROM into RDAC	
14	1	0	1	1	X	X	X	X	X	X	X	X	X	X	X	X	X	Software reset	
15	1	1	0	0	A3	0	0	A0	X	X	X	X	X	X	X	X	D0	Software shutdown	
																	D0	Condition	
																	0	Normal mode	
																	1	Shutdown mode	

¹X means don't care.

Table 11. Reduced Address Bits Table

A3	A2	A1	A0	Channel	Stored Channel Memory
1	X ¹	X ¹	X ¹	All channels	Not applicable
0	0	0	0	RDAC1	RDAC1
0	0	0	1	RDAC2	Not applicable
0	0	1	0	Not applicable	RDAC2

¹X means don't care.

ADVANCED CONTROL MODES

The AD5122/AD5142 digital potentiometers include a set of user programming features to address the wide number of applications for these universal adjustment devices (see Table 16 and Table 18).

Key programming features include the following:

- Input register
- Linear gain setting mode
- Low wiper resistance feature
- Lineal increment and decrement instructions
- ± 6 dB increment and decrement instructions
- Reset
- Shutdown mode

Input Register

The AD5122/AD5142 include one input register per RDAC register. These registers allow preloading of the value for the associated RDAC register. These registers can be written to using Command 2 and read back from using Command 3 (see Table 16).

This feature allows a synchronous update of one or all the RDAC registers at the same time.

The transfer from the input register to the RDAC register is done synchronously by Command 8 (see Table 16).

If new data is loaded into an RDAC register, this RDAC register automatically overwrites the associated input register.

Linear Gain Setting Mode

The proprietary architecture of the AD5122/AD5142 allows the independent control of each string resistor, R_{AW} and R_{WB} . To enable this feature, use Command 16 (see Table 16) to set Bit D2 of the control register (see Table 18).

This mode of operation can control the potentiometer as two independent rheostats connected at a single point, W terminal, as opposed to potentiometer mode where each resistor is complementary, $R_{AW} = R_{AB} - R_{WB}$.

This feature enables a second input and an RDAC register per channel, as shown in Table 17; however, the actual RDAC contents remain unchanged. The same operations are valid for potentiometer mode and linear gain setting mode.

If the INDEP pin is pulled high, the device powers up in linear gain setting mode and loads the values stored in the associated memory locations for each channel (see Table 17). The INDEP pin and D2 bit are connected internally to a logic or gate, if any or both are 1, the devices cannot operate in potentiometer mode.

Low Wiper Resistance Feature

The AD5122/AD5142 include two commands to reduce the wiper resistance between the terminals when the devices achieve full scale or zero scale. These extra positions are called bottom scale, BS, and top scale, TS. The resistance between Terminal A and Terminal W at top scale is specified as R_{TS} . Similarly, the bottom scale resistance between Terminal B and Terminal W is specified as R_{BS} .

The contents of the RDAC registers are unchanged by entering in these positions. There are three ways to exit from top scale and bottom scale: by using Command 12 or Command 13 (see Table 16); by loading new data in an RDAC register, which includes increment/decrement operations; or by entering shutdown mode, Command 15 (see Table 16).

Table 12 and Table 13 show the truth tables for the top scale position and the bottom scale position, respectively, when the potentiometer or linear gain setting mode is enabled.

Table 12. Top Scale Truth Table

Linear Gain Setting Mode		Potentiometer Mode	
R_{AW}	R_{WB}	R_{AW}	R_{WB}
R_{AB}	R_{AB}	R_{TS}	R_{AB}

Table 13. Bottom Scale Truth Table

Linear Gain Setting Mode		Potentiometer Mode	
R_{AW}	R_{WB}	R_{AW}	R_{WB}
R_{TS}	R_{BS}	R_{AB}	R_{BS}

Linear Increment and Decrement Instructions

The increment and decrement commands (Command 4 and Command 5 in Table 16) are useful for linear step adjustment applications. These commands simplify microcontroller software coding by allowing the controller to send an increment or decrement command to the device. The adjustment can be individual or in a ganged potentiometer arrangement, where all wiper positions are changed at the same time.

For an increment command, executing Command 4 automatically moves the wiper to the next RDAC position. This command can be executed in a single channel or multiple channels.

±6 dB Increment and Decrement Instructions

Two programming instructions produce logarithmic taper increment or decrement of the wiper position control by an individual potentiometer or by a ganged potentiometer arrangement where all RDAC register positions are changed simultaneously. The +6 dB increment is activated by Command 6, and the –6 dB decrement is activated by Command 7 (see Table 16). For example, starting with the zero-scale position and executing Command 6 ten times moves the wiper in 6 dB steps to the full-scale position. When the wiper position is near the maximum setting, the last 6 dB increment instruction causes the wiper to go to the full-scale position (see Table 14).

Incrementing the wiper position by +6 dB essentially doubles the RDAC register value, whereas decrementing the wiper position by –6 dB halves the register value. Internally, the AD5122/AD5142 use shift registers to shift the bits left and right to achieve a ±6 dB increment or decrement. These functions are useful for various audio/video level adjustments, especially for white LED brightness settings in which human visual responses are more sensitive to large adjustments than to small adjustments.

Table 14. Detailed Left Shift and Right Shift Functions for the ±6 dB Step Increment and Decrement

Left Shift (+6 dB/Step)	Right Shift (–6 dB/Step)
0000 0000	1111 1111
0000 0001	0111 1111
0000 0010	0011 1111
0000 0100	0001 1111
0000 1000	0000 1111
0001 0000	0000 0111
0010 0000	0000 0011
0100 0000	0000 0001
1000 0000	0000 0000
1111 1111	0000 0000

Reset

The AD5122/AD5142 can be reset through software by executing Command 14 (see Table 16) or through hardware on the low pulse of the RESET pin. The reset command loads the RDAC registers with the contents of the EEPROM and takes approximately 30 μs. The EEPROM is preloaded to midscale at the factory, and initial power-up is, accordingly, at midscale. Tie RESET to V_{LOGIC} if the RESET pin is not used.

Shutdown Mode

The AD5122/AD5142 can be placed in shutdown mode by executing the software shutdown command, Command 15 (see Table 16); and by setting the LSB (D0) to 1. This feature places the RDAC in a special state. The contents of the RDAC register are unchanged by entering shutdown mode. However, all commands listed in Table 16 are supported while in shutdown mode. Execute Command 15 (see Table 16) and set the LSB (D0) to 0 to exit shutdown mode.

Table 15. Truth Table for Shutdown Mode

A2	Linear Gain Setting Mode		Potentiometer Mode	
	AW	WB	AW	WB
0	N/A ¹	Open	Open	R _{BS}
1	Open	N/A ¹	N/A ¹	N/A ¹

¹ N/A means not applicable.

EEPROM OR RDAC REGISTER PROTECTION

The EEPROM and RDAC registers can be protected by disabling any update to these registers. This can be done by using software or by using hardware. If these registers are protected by software, set Bit D0 and/or Bit D1 (see Table 18), which protects the EEPROM and RDAC registers independently.

When RDAC is protected, the only operation allowed is to copy the EEPROM into the RDAC register.

INDEP PIN

If the INDEP pin is pulled high at power-up, the device operates in linear gain setting mode, loading each string resistor, R_{AWx} and R_{WBx}, with the value stored into the EEPROM (see Table 17). If the pin is pulled low, the device powers up in potentiometer mode.

The INDEP pin and the D2 bit are connected internally to a logic OR gate, if any or both are 1, the device cannot operate in potentiometer mode (see Table 18).

Table 16. Advance Command Operation Truth Table

Command Number	Control Bits[DB15:DB12]				Address Bits[DB11:DB8] ¹				Data Bits[DB7:DB0] ¹								Operation		
	C3	C2	C1	C0	A3	A2	A1	A0	D7	D6	D5	D4	D3	D2	D1	D0			
0	0	0	0	0	X	X	X	X	X	X	X	X	X	X	X	X	NOP: do nothing		
1	0	0	0	1	0	A2	0	A0	D7	D6	D5	D4	D3	D2	D1	D0	Write contents of serial register data to RDAC		
2	0	0	1	0	0	A2	0	A0	D7	D6	D5	D4	D3	D2	D1	D0	Write contents of serial register data to input register		
3	0	0	1	1	0	A2	A1	A0	X	X	X	X	X	X	D1	D0	Read back contents		
																	D1	D0	Data
																	0	0	Input register
																	0	1	EEPROM
1	0	Control register																	
1	1	RDAC																	
4	0	1	0	0	A3	A2	0	A0	X	X	X	X	X	X	X	1	Linear RDAC increment		
5	0	1	0	0	A3	A2	0	A0	X	X	X	X	X	X	X	0	Linear RDAC decrement		
6	0	1	0	1	A3	A2	0	A0	X	X	X	X	X	X	X	1	+6 dB RDAC increment		
7	0	1	0	1	A3	A2	0	A0	X	X	X	X	X	X	X	0	-6 dB RDAC decrement		
8	0	1	1	0	A3	A2	0	A0	X	X	X	X	X	X	X	X	Copy input register to RDAC (software LRDAC)		
9	0	1	1	1	0	A2	0	A0	X	X	X	X	X	X	X	1	Copy RDAC register to EEPROM		
10	0	1	1	1	0	A2	0	A0	X	X	X	X	X	X	X	0	Copy EEPROM into RDAC		
11	1	0	0	0	0	0	A1	A0	D7	D6	D5	D4	D3	D2	D1	D0	Write contents of serial register data to EEPROM		
12	1	0	0	1	A3	A2	0	A0	1	0	0	0	0	0	0	D0	Top scale D0 = 0; normal mode D0 = 1; shutdown mode		
13	1	0	0	1	A3	A2	0	A0	0	0	0	0	0	0	0	D0	Bottom scale D0 = 1; enter D0 = 0; exit		
14	1	0	1	1	X	X	X	X	X	X	X	X	X	X	X	X	Software reset		
15	1	1	0	0	A3	A2	0	A0	0	0	0	0	0	0	0	D0	Software shutdown D0 = 0; normal mode D0 = 1; device placed in shutdown mode		
16	1	1	0	1	X	X	X	X	X	X	X	X	D2	D1	D0	Copy serial register data to control register			

¹ X means don't care.